

L Number	Hits	Search Text	DB	Time stamp
-	628447	DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:54
-	12833	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50
-	3878	(DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:55
-	34706	(bury or buried) near3 (layer\$1 or film\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 11:56
-	753	((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40
-	0	20040014329.URPN.	USPAT	2004/03/15 12:00
-	268974	source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:40
-	16200	(remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:42
-	756023	(top or upper or second) near4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:43
-	121	((((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:44
-	47376	storag\$4 near4 (plate\$1 or electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:45

-	53	((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1)) and (((DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1))) and ((bury or buried) near3 (layer\$1 or film\$1))) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1))) and (storag\$4 near4 (plate\$1 or electrode\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 12:49
-	758663	(lower or bottom or first) near4 (electrode\$1 or plate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:42
-	968	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or (438/248) or (438/249)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:45
-	741	((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:46
-	1293	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or (438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.)	USPAT; US-PGPUB	2004/03/15 15:47
-	1892	((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or (438/242) or (438/268) or (438/270) or (438/271)).CCLS.	USPAT; US-PGPUB	2004/03/15 15:50
-	46651	vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 15:50
-	124	(vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and ((bury or buried) near3 (layer\$1 or film\$1)) and (source\$1 and drain\$1) and ((remov\$4 or etch\$4) same drain\$1 same (substrate or wafer) same (hole\$1 or trench\$2 or via\$1 or open\$5 or groov\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower or bottom or first) near4 (electrode\$1 or plate\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:08
-	131	((438/136) or (438/137) or (438/138) or (438/206) or (438/241) or (438/242) or (438/268) or (438/270) or (438/271)).CCLS.) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower or bottom or first) near4 (electrode\$1 or plate\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09
-	129	((438/243) or (438/244) or (438/245) or (438/246) or (438/247) or (438/248) or (438/249)).CCLS.) or (((438/386) or (438/387) or (438/388) or (438/389) or (438/390) or (438/391) or (438/392)).CCLS.) and (DRAM\$1 or (dynamic adj random adj access adj memor\$4) or capacitor\$1) and (vertical\$4 near3 (MOS or transistor\$1 or MOSFET\$1 or channel\$3)) and ((top or upper or second) near4 (plate\$1 or electrode\$1)) and ((storag\$4 near4 (plate\$1 or electrode\$1)) or ((lower or bottom or first) near4 (electrode\$1 or plate\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 16:09